

ABSTRACT OF THE DISCLOSURE

A method of forming a patterned photoresist with a non-distorted profile. A first photoresist is formed on a substrate. The first photoresist is suitable for patterning a trench pattern. A second photoresist is formed on the first photoresist. The second photoresist is suitable for patterning an iso-line pattern. A photolithography step is then performed to pattern the second and the first photoresist to form a patterned photoresist.